

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1-2. (canceled)

3. (currently amended) The process as defined in claim [[1]] 5, wherein the formation of the rough surface of said interlayer insulating film and the second opening is conducted by halftone exposure or two-times exposure.

4. (previously presented) The process as defined in claim 3, wherein the formation of the rough surface of said interlayer insulating film and the second opening is conducted by using the fourth mask having controlled transmissivity.

5. (currently amended) A process for producing a reflection type liquid crystal display device, comprising the steps of:

(a) depositing a low resistance metal layer on an insulating substrate, and using a first mask to pattern the metal layer to form source/drain electrodes;

(b) depositing a silicon layer, gate insulating film and gate electrode layer on said insulating substrate having said source/drain electrodes formed thereon in this order, and using a second mask to pattern the silicon layer, the gate insulating film and the gate electrode layer to form a thin film transistor region and a gate electrode;

(c) depositing a passivation film on said insulating substrate having said source/drain electrodes, said thin film transistor region and said gate electrode formed thereon, and using a third mask to form a first opening through said passivation film to said source electrode;

(d) depositing an interlayer insulating film on said passivation film, forming a rough surface of said interlayer insulating film, and using a fourth mask to form a second opening through said interlayer insulating film at a position corresponding to the first opening;

(e) depositing a reflective metal over the rough surface of said interlayer insulating film to form a reflection electrode extended and electrically connected to said source electrode through the first and second openings

(f) forming a first capacitor electrode when said source/drain electrodes are formed; and

(g) forming a second capacitor electrode when said gate electrode layer is formed; and

[[(g)]] (h) forming a third opening for a storage capacitor through said interlayer insulating film and said passivation film in a position on said first capacitor electrode when the first and second openings are formed,

wherein said reflection electrode extends through the third opening and is electrically connected to said first capacitor electrode.

6. (cancelled).

7. (currently amended) The process as defined in claim [[1]] 5, further comprising the step of heat treating at least the rough surface of said interlayer insulating film before depositing said reflective metal and after forming the rough surface of said interlayer insulating film.

8. (currently amended) The process as defined in claim [[1]] 5, further comprising the step of treating at least said source/drain electrodes with PH_3 after said source/drain electrodes are formed and prior to successive deposition of said silicon layer, gate insulating film and gate electrode layer.

9-16. (canceled)